

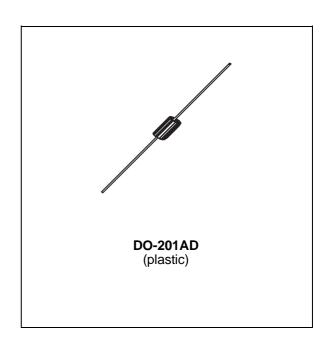
HIGH VOLTAGE ULTRA-FAST DIODE FOR VIDEO

MAJOR PRODUCT CHARACTERISTICS

I _{Fpeak}	4 A
V _{RRM}	600 V
t _{rr}	55 ns
V _F (max)	1.2 V

FEATURES AND BENEFITS

- TURBOSWITCH[™] OUTSTANDING BENEFITS.
- HIGH REVERSE VOLTAGE: 600 V
- LOW POWER LOSSES INDUCING LOW TEMPERATURE AND HIGH RELIABILITY.
- OPTIMIZED TRADE-OFF BETWEEN t_{rr} AND SOFTNESS FOR VIDEO HORIZONTAL DEFLECTION.



DESCRIPTION

High voltage ultra-fast diode especially designed for modulation and flyback rectification in standard and high resolution displays for TV's and monitors.

The device is packaged in a DO-201AD axial enveloppe.

ABSOLUTE RATINGS (limiting values)

Symbol	Paramete	VALUE	Unit	
VRRM	Repetitive peak reverse voltage	600	V	
I _F peak	Forward peak current (1)	4	А	
I _{FRM}	Repetitive peak forward current	tp=5µs F=1kHz square	100	А
I _{FSM}	Surge non repetitive forward current	• • • • • • • • • • • • • • • • • • • •		А
T _{stg}	Storage temperature range	- 40 to 150	°C	
Tj	Maximum operating junction to	150	°C	

⁽¹⁾ on infinite heatsink with 10mm lead length

August 1999 - Ed: 4A 1/4

MDV04-600

THERMAL RESISTANCES

Symbol	Parameter	Max.	Unit
R _{th(j-l)}	Junction to lead	20	°C/W
R _{th(j-a)}	Junction to ambient on printed circuit L lead = 10mm	75	°C/W

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Con	Тур.	Max.	Unit	
l _R *	Reverse leakage current	V _R = 480V	Tj = 25°C Tj = 125°C		50 0.75	μA mA
V _F **	Forward voltage drop	I _F = 4 A	Tj = 25°C Tj = 125°C		1.28 1.20	V

DYNAMIC ELECTRICAL CHARACTERISTICS

TURN-OFF SWITCHING

Symbol	Parameter	Test Conditions	Тур.	Max.	Unit
t _{rr}	Reverse recovery time	$I_F = 0.5A$ $I_R = 1A$ Irr = 0.25A	55	75	ns
		$I_F = 100 \text{ mA}$ $I_R = 100 \text{ mA}$ $I_{rr} = 10 \text{mA}$	130		ns

DYNAMIC ELECTRICAL CHARACTERISTICS

TURN-ON SWITCHING

Symbol	Parameter	Тур.	Max.	Unit	
t _{fr}	Forward recovery time	I _F = 4 A dI _F /dt = 100 A/μs		0.5	μs
V _{FP}	Peak forward voltage	Measured at1.1 x V _F max. Tj = 25℃		15	V

To evaluate the maximum conduction losses use the following equation :

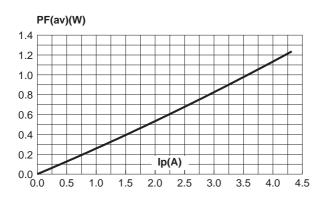
$$P = \frac{1.0 \ x \ l_p}{2} x \ \delta + \frac{0.050 \ x \ l_p^2}{3} \ x \ \delta$$

 $\boldsymbol{\delta}$: duty cycle Ip: Peak current

Ex : for $I_p = 4$ A and $\delta = 0.5$, P = 1.2 Watts.

Pulse test : * tp = 5 ms, δ < 2% ** tp = 380 μ s, δ < 2%

Fig. 1: Power dissipation versus peak forward current (triangular waveform, δ =0.5).



t(s)

1E+0

1E+1

1E+2

Fig. 2: Relative variation of thermal impedance

junction to ambient versus pulse duration (epoxy printed circuit board, $e(Cu)=35\mu m$), recommended

pad layout).

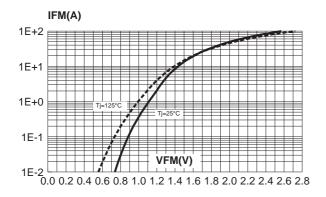
1E-2

1E-2

Fig. 3: Forward voltage drop versus forward current (maximum values).

Fig. 4: Reverse recovery time versus dIF/dt.

1E-1



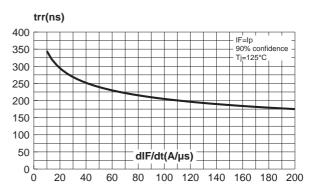
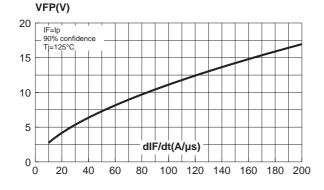
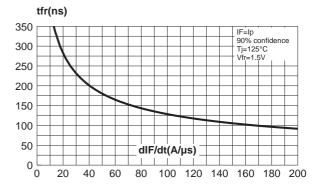


Fig. 5: Transient peak forward voltage versus dIF/dt.

Fig. 6: Forward recovery time versus dIF/dt.

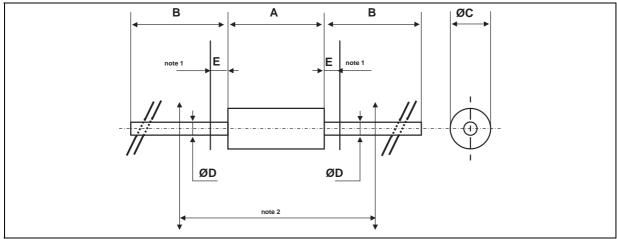




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PACKAGE MECHANICAL DATA

DO-201AD



		DIMENSIONS			
REF.	Millim	neters	Inc	hes	NOTES
	Min.	Max.	Min.	Max.	
Α		9.50		0.374	1 - The lead diameter Ø D is not controlled over zone E
В	25.40		1.000		2 - The minimum axial length within which the device may be
ØC		5.30		0.209	placed with its leads bent at right angles is 0.59"(15 mm)
ØD		1.30		0.051	
Е		1.25		0.049	

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
MDV04-600	MDV04-600	DO-201AD	1.166g.	600	Ammopack
MDV04-600RL	MDV04-600	DO-201AD	1.166g.	1900	Tape & reel

- Epoxy meets UL94,V0
- Polarity : Cathode indicated by polarity band

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